

High Isolation SPDT Switch

Description

The CXG1009TN is a high Isolation SPDT (Single Pole Dual Throw) switch MMIC for personal communication, cable TV and so on.

This IC is designed using the Sony's GaAs J-FET process and operates at a single positive control supply.

Features

- Single positive control supply operation
- Insertion Loss
 - 0.7 dB (Typ.) @1.0 GHz, $V_{ctl} (H)=3\text{ V}$
 - 0.8 dB (Typ.) @2.0 GHz, $V_{ctl} (H)=3\text{ V}$
- High Isolation
 - 56 dB (Typ.) @1.0 GHz, $V_{ctl} (H)=3\text{ V}$
 - 47 dB (Typ.) @2.0 GHz, $V_{ctl} (H)=3\text{ V}$
- 10pin TSSOP package (3.2 × 2.8 mm)

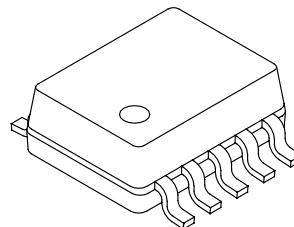
Applications

- Basestation Lo switching.
- Other Low Power SPDT applications requiring high isolation (e.g. Cable TV).

Structure

GaAs J-FET MMIC

10 pin TSSOP (Plastic)



Absolute Maximum Ratings (Ta=25 °C)

- | | | | |
|-------------------------|-----------------------------|-------------|----|
| • Control voltage | $V_{ctl} (H) - V_{ctl} (L)$ | 6 | V |
| • Control Current | I_{ctl} | 2 | mA |
| • Operating temperature | T_{opr} | -35 to +85 | °C |
| • Storage temperature | T_{stg} | -65 to +150 | °C |

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Electrical Characteristics

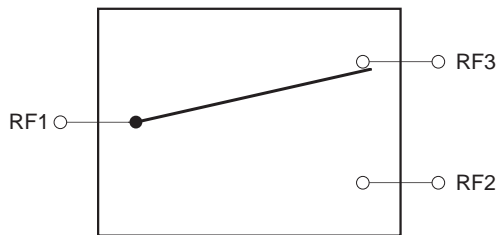
V_{CTL} (L) =0 V, V_{CTL} (H) =3 V, P_{in}=10 dBm

(T_a=25 °C)

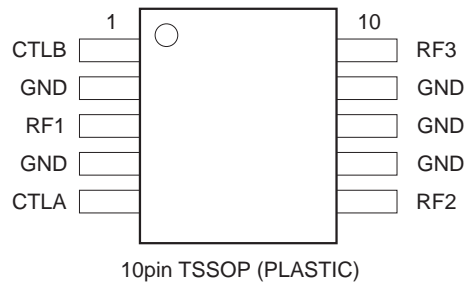
| Item | Symbol | Condition | MIN. | TYP. | MAX. | UNit |
|------------------|------------------|---------------------|------|------|------|------|
| Insertion Loss 1 | IL1 | f ≤ 1 GHz | | 0.7 | 1.1 | dB |
| Isolation 1 | ISO1 | | 52 | 56 | | dB |
| Insertion Loss 2 | IL2 | f ≤ 2 GHz | | 0.8 | 1.2 | dB |
| Isolation 2 | ISO2 | | 43 | 47 | | dB |
| VSWR | VSWR | | | 1.2 | 1.5 | |
| Switching Speed | TSW | | | 100 | | ns |
| Control Current | I _{CTL} | | | 60 | 200 | μA |
| 1 dB Compression | P1dB | 500 MHz ≤ f ≤ 2 GHz | 16 | 19 | | dBm |
| | | f = 5 MHz | | 8 | | dBm |

50 Ω source and load impedance

Block Diagram

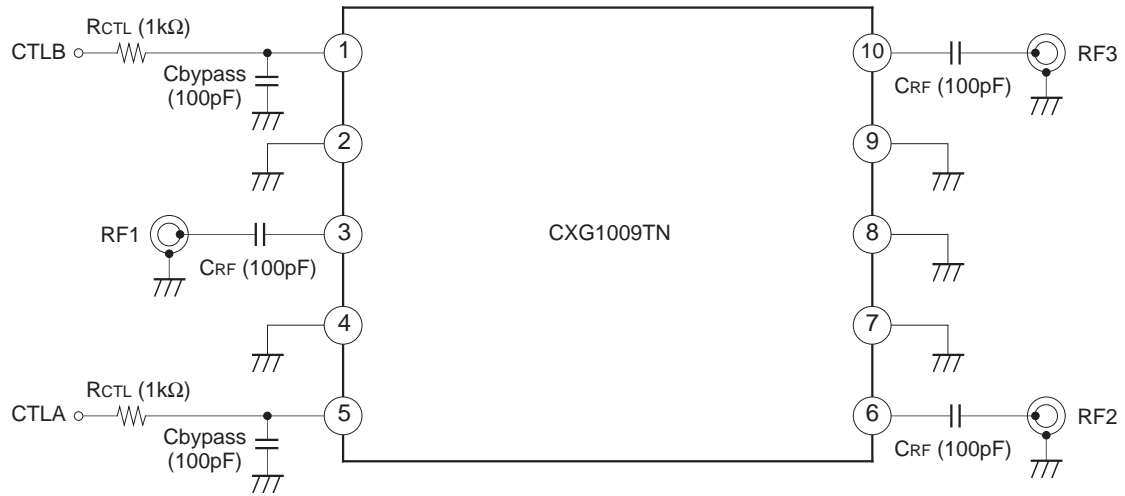


Package Outline/Pin Configuration



| V _{CTLA} | V _{CTLB} | |
|-------------------|-------------------|---------------------------|
| High | Low | RF1-RF2 ON RF1-RF3 OFF |
| Low | High | RF1-RF2 OFF RF1-RF3 ON |

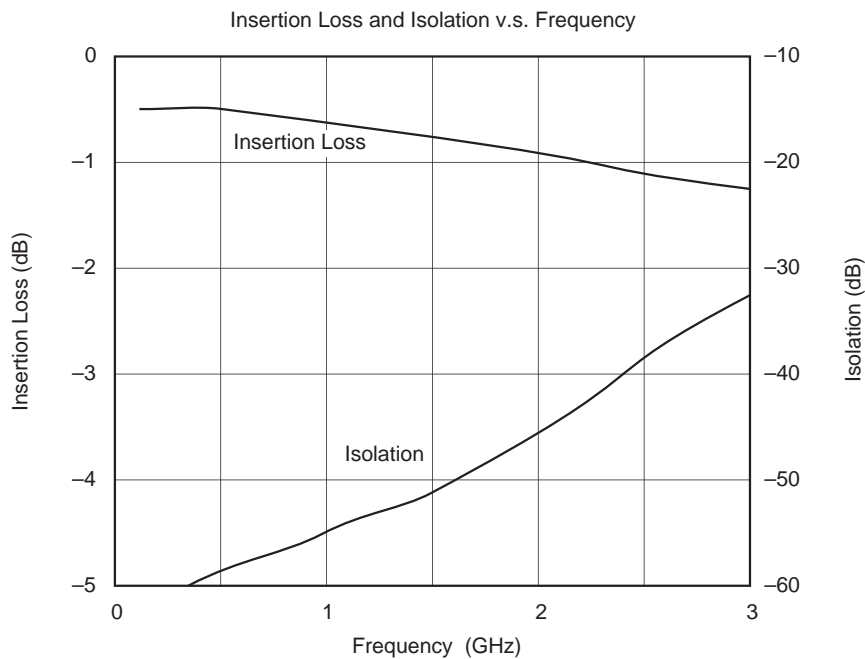
Recommended Circuit



- * It is necessary to use DC blocking capacitors C_{RF} and bypass capacitors C_{bypass} .
- * It is necessary to use control resistors R_{CTL} , if current consumption needs to be reduced or ESD performance needs to be improved.
- * It is necessary to operate at low frequency, DC blocking capacitors C_{RF} needs higher values.

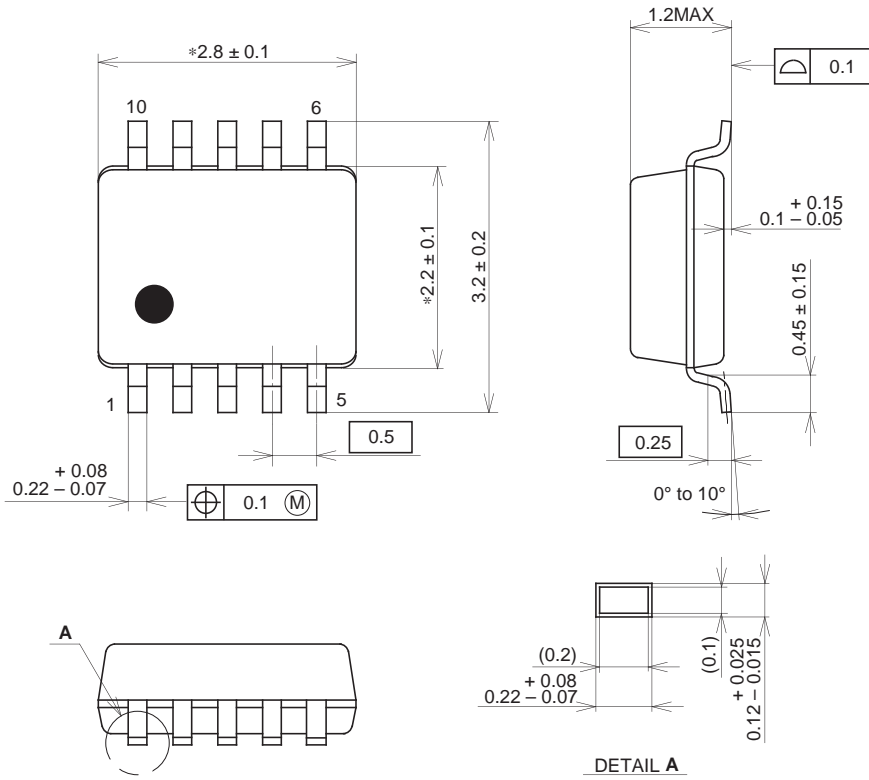
Frequency characteristics

Measurement Conditions : $V_{ctl(L)} = 0\text{ V}$, $V_{ctl(H)} = 3\text{ V}$, $P_{in} = 0\text{ dBm CW}$, $T = 25\text{ °C}$



Package Outline Unit : mm

10PIN TSSOP(PLASTIC)



NOTE: Dimension "*" does not include mold protrusion.

PACKAGE STRUCTURE

| | |
|------------|---------------|
| SONY CODE | TSSOP-10P-L01 |
| EIAJ CODE | _____ |
| JEDEC CODE | _____ |

| | |
|------------------|----------------|
| PACKAGE MATERIAL | EPOXY RESIN |
| LEAD TREATMENT | SOLDER PLATING |
| LEAD MATERIAL | COPPER ALLOY |
| PACKAGE MASS | 0.02g |